



RECEIVED
NOV 19 2002
TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

)

Art Unit: 2829

Shunpei YAMAZAKI et al.

)

Examiner: A Sakar

Serial No. 09/699,466 ✓

)

Filed: October 31, 2000 ✓

)

For: METHOD FOR FABRICATING A)

SEMICONDUCTOR DEVICE)

)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
The United States Postal Service with sufficient postage as First
Class Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on 11/6/02

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated August 6, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 4-34 and amend claim 1 as follows:

1. (Amended) A method for manufacturing a semiconductor device comprising:
- forming a semiconductor film on an insulating surface;
 - forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;
 - forming a first gate insulating film over the semiconductor island wherein the first gate insulating film comprises silicon oxide;
 - forming a second gate insulating film over the first gate insulating film wherein the second gate insulating film comprises silicon oxide nitride;
 - forming a gate electrode over the semiconductor island with the first gate insulating film and the second gate insulating film therebetween; and

11/18/2002 #ABDELRI 00000015 09699466 252.00 OP
02 FC:1201